

IR Laser Diode

Application

Industrial use / Biomedical

Property

Wavelength $\lambda = 780$ nm

Output Power = 5mW

Package Type = ϕ 5.6mm

Introduction

Egismos currently markets AlGaAs infrared laser diodes in the 780nm ~ 1550nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers, blue laser DVD, laser barcode scanners, diode laser equipments, medical instruments and aerospace applications.



IR Laser Diode Key features

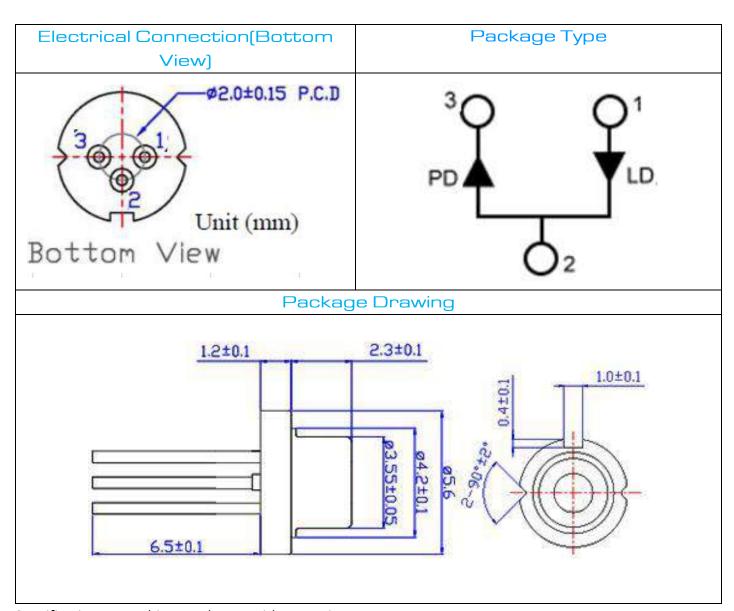
Absolute Maximum Rating at Tc=25℃						
Items	Symbols	Values	Unit			
Optical Output Power	Po(CW)	5	mW			
Reverse Voltage	V	2	V			
Operating Temperature	То	-10~+60	$^{\circ}$ C			
Storage Temperature	Ts	-10~+70	$^{\circ}$			

Electrical and Optical Characteristics at Tc=25℃							
Item	Symbols	Min	Тур.	Max.	Unit	Condition	
Optical Output Power	Ро	-	-	5	mW	-	
Threshold Current	Ith	-	20	30	mA	-	
Operating Current	lop	-	30	40	mA	Po=5mW	
Operating Voltage	Vop	-	1.9	2.3	V	Po=5mW	
Peak Wavelength	λр	770	780	795	nm	Po=5mW	



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<u>EGISMOS</u>	780nm Laser Diode				D6-6-780-5-P	
Beam Divergence	θ//	8	11	15	deg	Po=5mW
	0	25	34	40	deg	Po=5mW



Specifications are subject to change without notice.





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